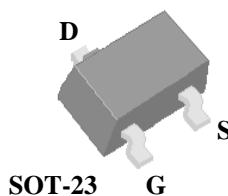
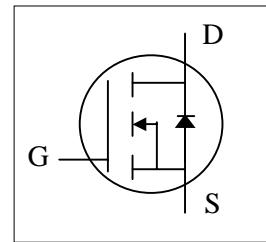




- ▼ Capable of 2.5V Gate Drive
- ▼ Small Outline Package
- ▼ Surface Mount Device
- ▼ Halogen Free & RoHS Compliant Product



BV_{DSS}	30V
$R_{DS(ON)}$	60m Ω
I_D	4A



Description

AP2328 series are from Advanced Power innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The special design SOT-23 package with good thermal performance is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.

Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	+12	V
$I_D @ T_A = 25^\circ\text{C}$	Drain Current ³ , $V_{GS} @ 4.5\text{V}$	4	A
$I_D @ T_A = 70^\circ\text{C}$	Drain Current ³ , $V_{GS} @ 4.5\text{V}$	3	A
I_{DM}	Pulsed Drain Current ¹	16	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation	1.38	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	90	°C/W



Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=4\text{A}$	-	-	55	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=3\text{A}$	-	-	60	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=2\text{A}$	-	-	90	$\text{m}\Omega$
		$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.5	-	1.5	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=3\text{A}$	-	15	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	10	uA
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_{\text{D}}=3\text{A}$	-	6	9.6	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=15\text{V}$	-	0.7	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=4.5\text{V}$	-	2.5	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time ²	$V_{\text{DS}}=15\text{V}$	-	5.3	-	ns
t_r	Rise Time	$I_{\text{D}}=1\text{A}$	-	9.5	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_{\text{G}}=3.3\Omega$	-	14.5	-	ns
t_f	Fall Time	$V_{\text{GS}}=5\text{V}$	-	4	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	325	520	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=25\text{V}$	-	50	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	45	-	pF
R_g	Gate Resistance	f=1.0MHz	-	2.1	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=1.2\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time ²	$I_{\text{S}}=3\text{A}, V_{\text{GS}}=0\text{V},$	-	15	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100\text{A}/\mu\text{s}$	-	8	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 270°C /W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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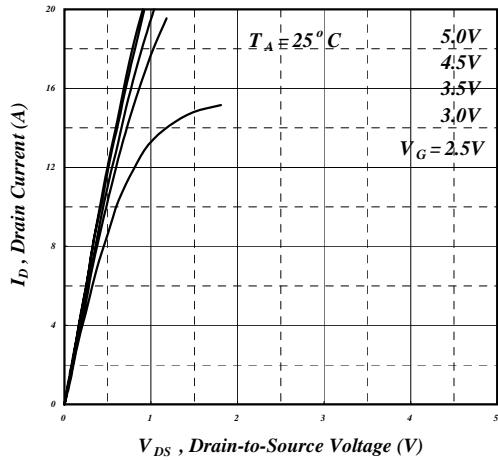


Fig 1. Typical Output Characteristics

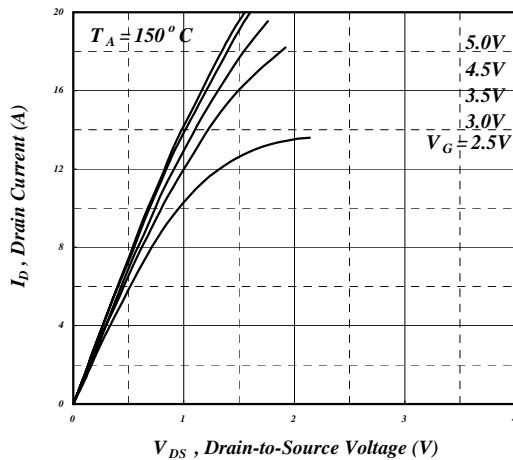


Fig 2. Typical Output Characteristics

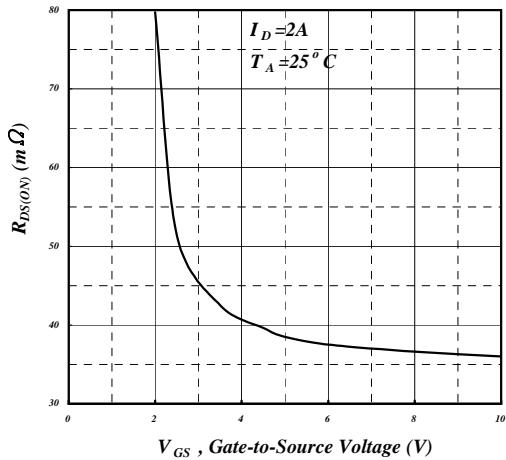


Fig 3. On-Resistance v.s. Gate Voltage

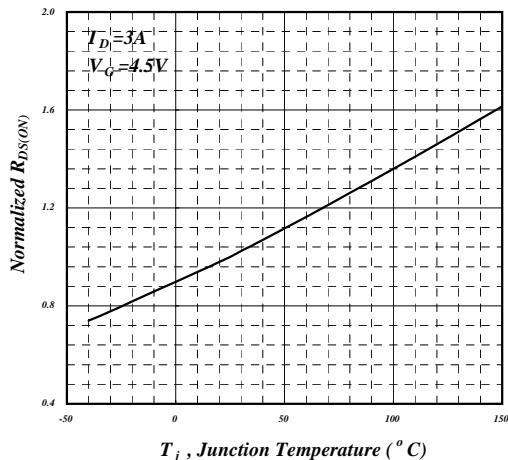


Fig 4. Normalized On-Resistance v.s. Junction Temperature

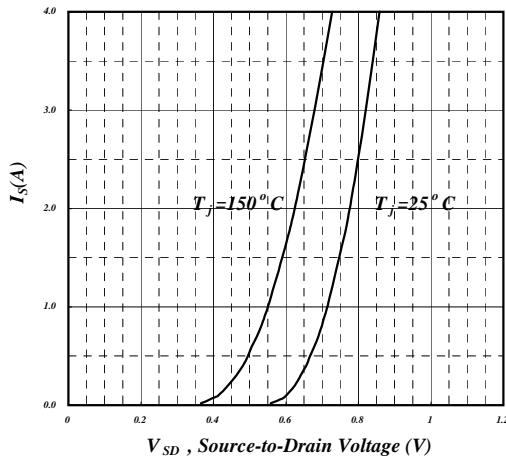


Fig 5. Forward Characteristic of Reverse Diode

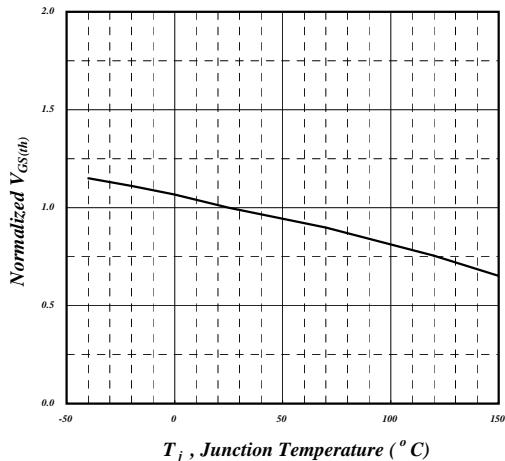
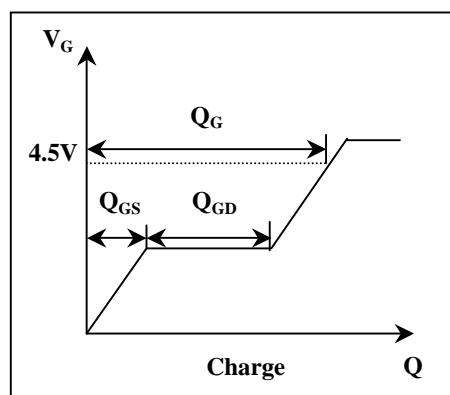
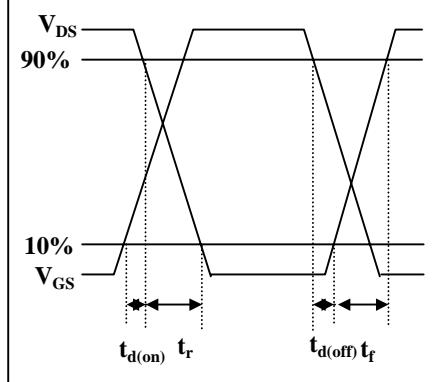
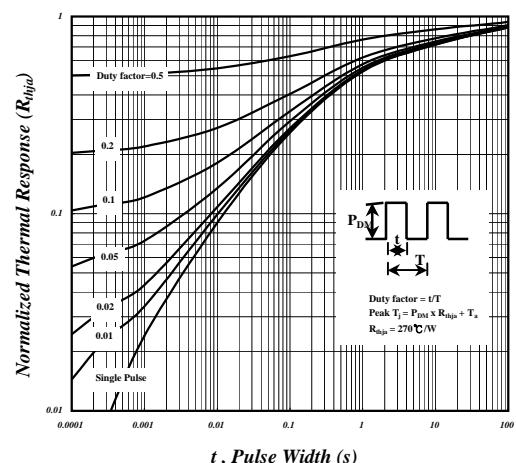
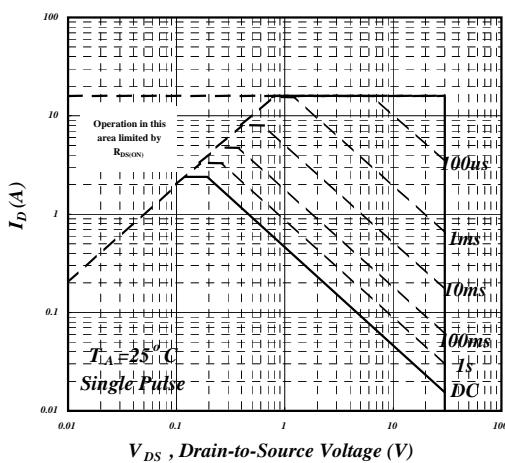
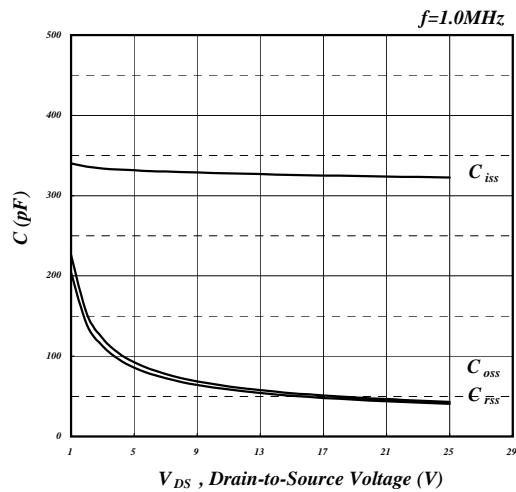
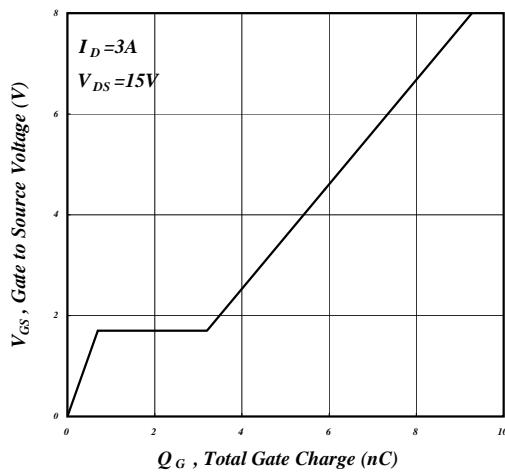


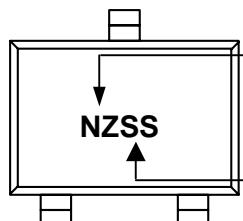
Fig 6. Gate Threshold Voltage v.s. Junction Temperature





AP2328GN-HF

MARKING INFORMATION



Part Number : NZ

Date Code : SS

SS:2004,2008,2012,2016,2020...

SS:2003,2007,2011,2015,2019...

SS:2002,2006,2010,2014,2018...

SS:2001,2005,2009,2013,2017...

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